

Silicon Diffused Power Transistor

BUJ304AX

GENERAL DESCRIPTION

High-voltage, high-speed planar-passivated npn power switching transistor in a plastic full-pack envelope intended for use in high frequency electronic lighting ballast applications, converters, inverters, switching regulators, motor control systems, etc.

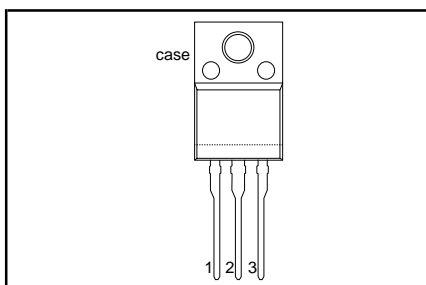
QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-------------|---------------------------------------|---|------|------|------|
| V_{CESM} | Collector-emitter voltage peak value | $V_{BE} = 0\text{ V}$ | - | 1000 | V |
| V_{CBO} | Collector-Base voltage (open emitter) | | - | 1000 | V |
| V_{CEO} | Collector-emitter voltage (open base) | | - | 500 | V |
| I_C | Collector current (DC) | | - | 6 | A |
| I_{CM} | Collector current peak value | | - | 10 | A |
| P_{tot} | Total power dissipation | $T_{hs} \leq 25\text{ }^\circ\text{C}$ | - | 32 | W |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 4.0\text{ A}; I_B = 0.8\text{ A}$ | 0.3 | 1.0 | V |
| h_{FEsat} | | $I_C = 4.0\text{ A}; V_{CE} = 5\text{ V}$ | 11 | 15 | |
| t_f | Fall time (Inductive) | $I_C = 5.0\text{ A}; I_{B1} = 1\text{ A}$ | 25 | 50 | ns |

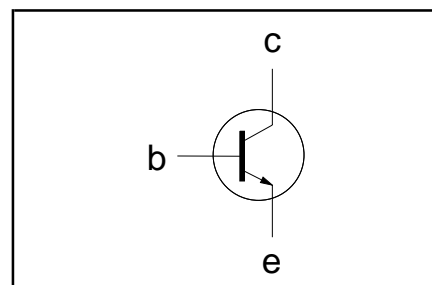
PINNING - SOT186A

| PIN | DESCRIPTION |
|------|-------------|
| 1 | base |
| 2 | collector |
| 3 | emitter |
| case | isolated |

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------|--|--|------|------|------------------|
| V_{CESM} | Collector to emitter voltage | $V_{BE} = 0\text{ V}$ | - | 1000 | V |
| V_{CEO} | Collector to emitter voltage (open base) | | - | 500 | V |
| V_{CBO} | Collector to base voltage (open emitter) | | - | 1000 | V |
| I_C | Collector current (DC) | | - | 6 | A |
| I_{CM} | Collector current peak value | | - | 10 | A |
| I_B | Base current (DC) | | - | 3 | A |
| I_{BM} | Base current peak value | | - | 6 | A |
| P_{tot} | Total power dissipation | $T_{hs} \leq 25\text{ }^\circ\text{C}$ | - | 32 | W |
| T_{stg} | Storage temperature | | -65 | 150 | $^\circ\text{C}$ |
| T_j | Junction temperature | | - | 150 | $^\circ\text{C}$ |

THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|----------------------|------------------------|------|------|------|
| $R_{th\ j-hs}$ | Junction to heatsink | With heatsink compound | - | 3.95 | K/W |
| $R_{th\ j-a}$ | Junction to ambient | in free air | 55 | - | K/W |

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ISOLATION LIMITING VALUE & CHARACTERISTIC $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|------------|--|--|------|------|------|------|
| V_{isol} | R.M.S. isolation voltage from all three terminals to external heatsink | $f = 50\text{-}60\text{ Hz}$; sinusoidal waveform; $R.H. \leq 65\%$; clean and dustfree | - | | 2500 | V |
| C_{isol} | Capacitance from T2 to external heatsink | $f = 1\text{ MHz}$ | - | 10 | - | pF |

STATIC CHARACTERISTICS $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|--|---|------|------|------|------|
| I_{CES}, I_{CBO} | Collector cut-off current ¹ | $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$ | - | - | 0.2 | mA |
| I_{CEO} | Collector cut-off current | $V_{CEO} = V_{CEOMmax}(500\text{ V})$ | - | - | 0.1 | mA |
| I_{EBO} | Emitter cut-off current | $V_{EB} = 9\text{ V}; I_C = 0\text{ A}$ | - | - | 1 | mA |
| $V_{CEOsust}$ | Collector-emitter sustaining voltage | $I_B = 0\text{ A}; I_C = 10\text{ mA};$ $L = 25\text{ mH}$ | 500 | - | - | V |
| V_{CEsat} | Collector-emitter saturation voltage | $I_C = 4.0\text{ A}; I_B = 0.8\text{ A}$ | - | 0.3 | 1.0 | V |
| V_{BEsat} | Base-emitter saturation voltage | $I_C = 4.0\text{ A}; I_B = 0.8\text{ A}$ | - | 1.0 | 1.3 | V |
| h_{FE} | DC current gain | $I_C = 5\text{ mA}; V_{CE} = 5\text{ V}$ | 10 | 17 | 34 | |
| h_{FEsat} | | $I_C = 500\text{ mA}; V_{CE} = 5\text{ V}$ | 14 | 22 | 34 | |
| | | $I_C = 4.0\text{ A}; V_{CE} = 5\text{ V}$ | 8 | 11 | 15 | |

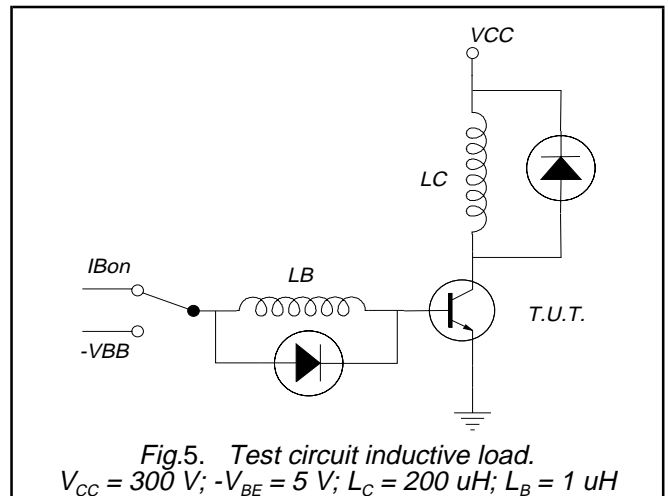
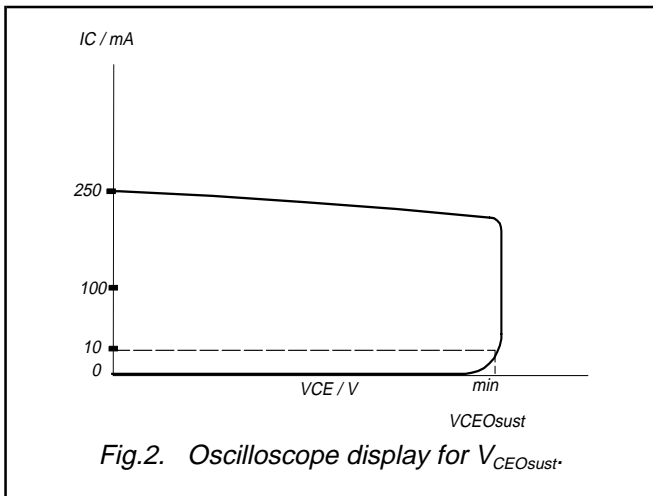
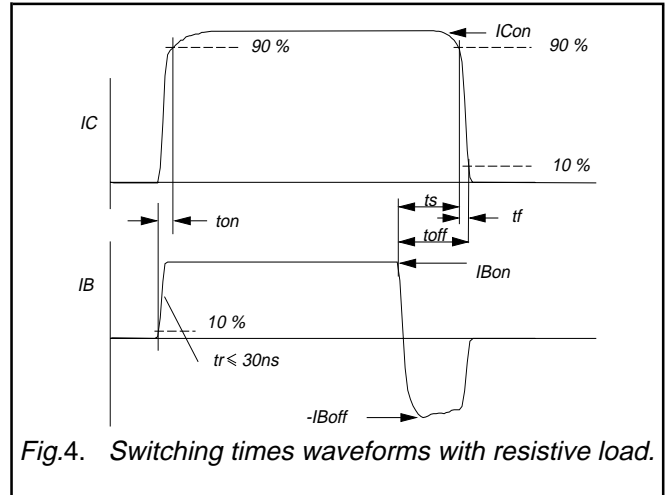
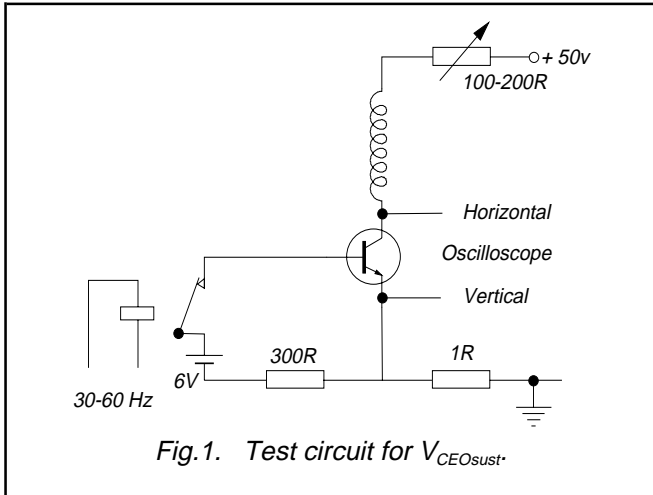
DYNAMIC CHARACTERISTICS $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------|----------------------------------|--|------|------|---------------|
| | Switching times (resistive load) | $I_{Con} = 5\text{ A}; I_{Bon} = -I_{Boff} = 1\text{ A};$ $R_L = 75\text{ ohms}; V_{BB2} = 4\text{ V};$ | | | |
| t_{on} | Turn-on time | | 0.8 | 1.0 | μs |
| t_s | Turn-off storage time | | 2.1 | 3.0 | μs |
| t_f | Turn-off fall time | | 375 | 527 | ns |
| | Switching times (inductive load) | $I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}$ | | | |
| t_s | Turn-off storage time | | 1.45 | 1.7 | μs |
| t_f | Turn-off fall time | | 25 | 50 | ns |
| | Switching times (inductive load) | $I_{Con} = 5\text{ A}; I_{Bon} = 1\text{ A}; L_B = 1\text{ }\mu\text{H};$ $-V_{BB} = 5\text{ V}; T_j = 100\text{ }^{\circ}\text{C}$ | | | |
| t_s | Turn-off storage time | | 1.64 | 2.2 | μs |
| t_f | Turn-off fall time | | 40 | 100 | ns |

¹ Measured with half sine-wave voltage (curve tracer).

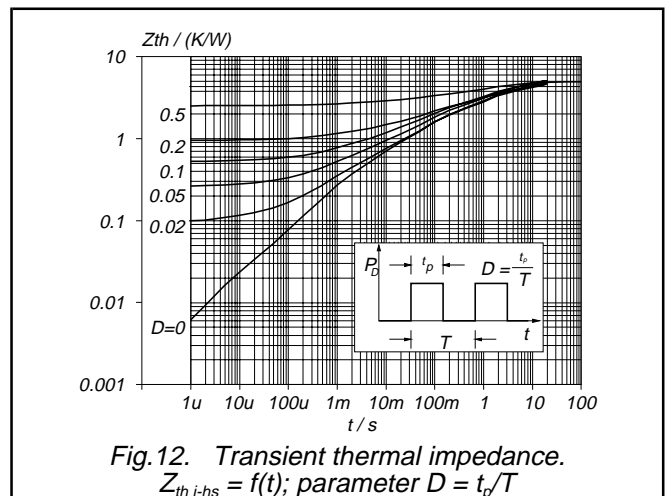
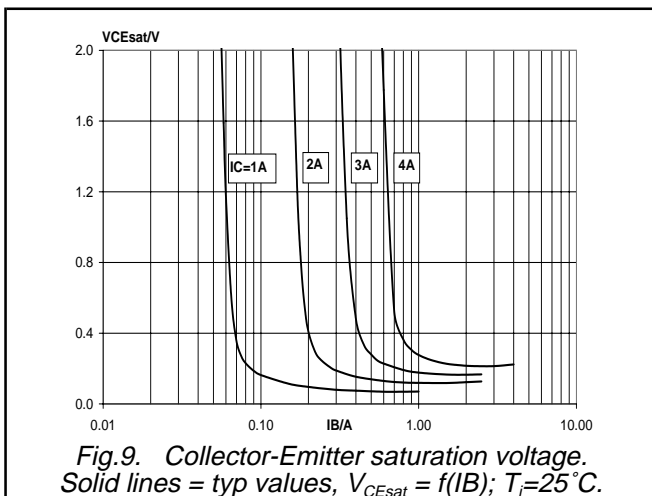
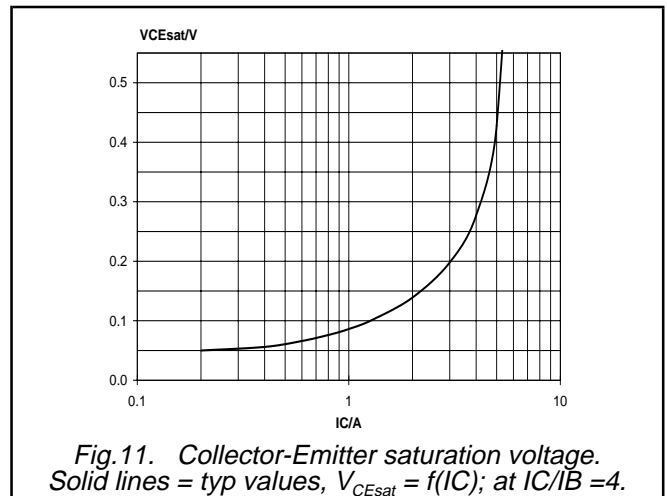
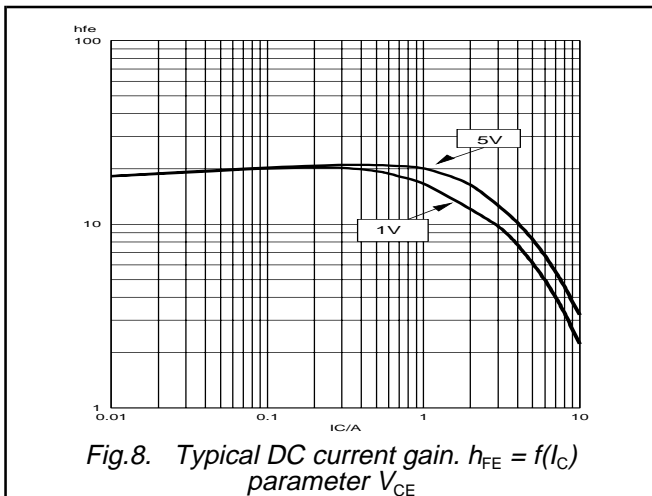
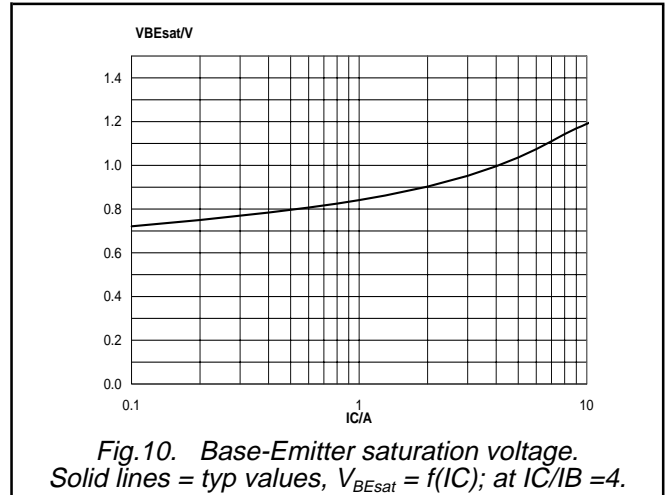
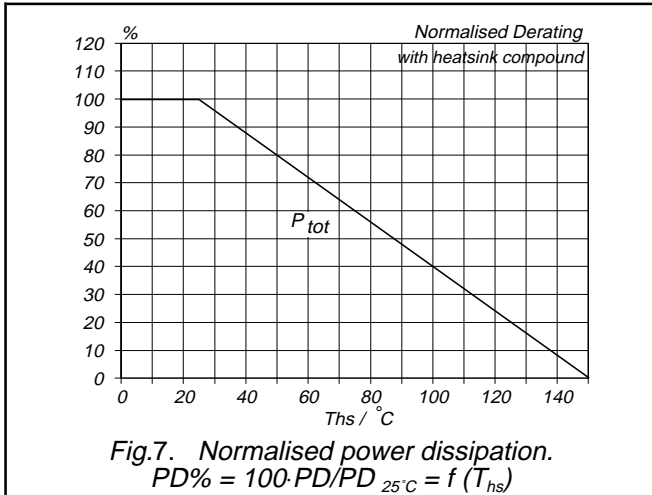
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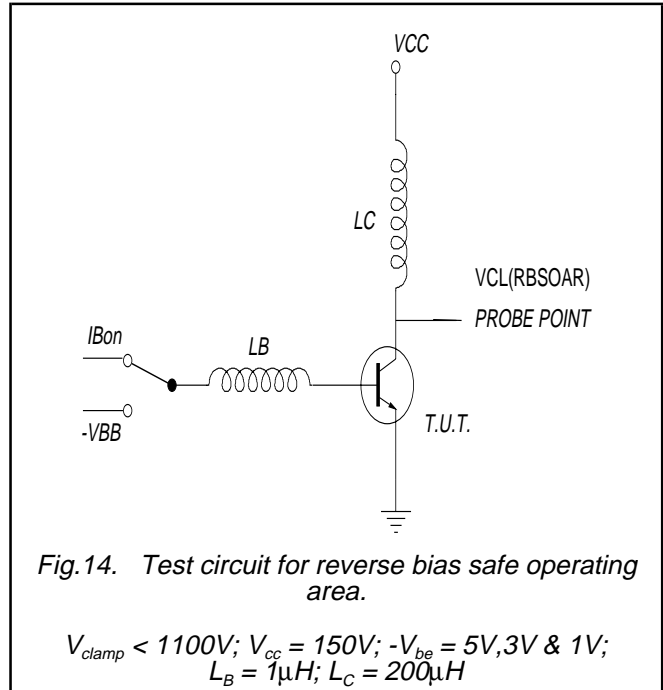
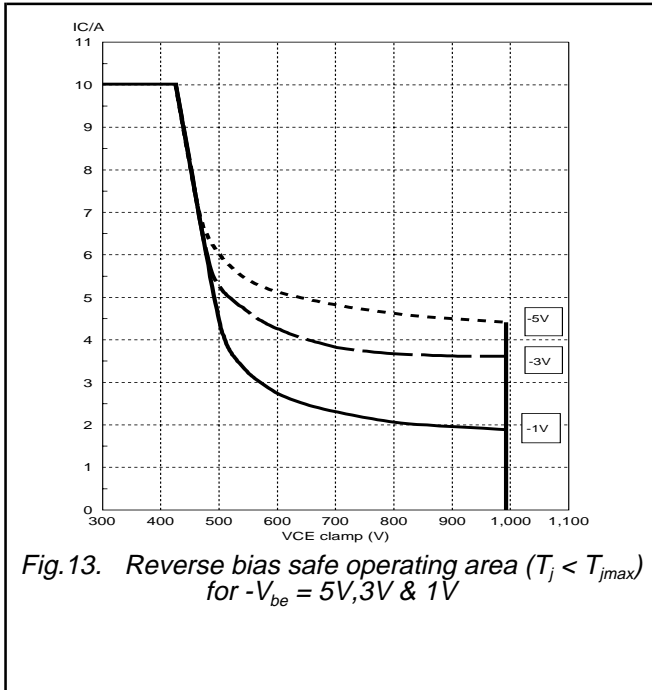
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DEFINITIONS

| | |
|--|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |
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